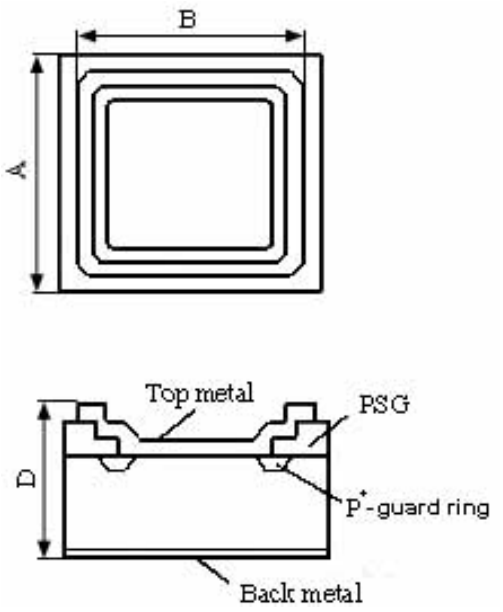
SCHOTTKY DIODES KDN-03040A.

PRELIMINARY

Rev.1. Feb. 2010

VSP-MIKRON	3A/40V. Die Size-60mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25˚C, I_F=3,0A	V_F	V	0,50	0,48
Maximum Reverse Current @ 25˚C, V_R=45V 25˚C, V_R=40V 125˚C, V_R=40V	I_R	mA	- 0,080 40,0	0,080 0,060 38,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	90	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	150	



DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	1520 1520
B_X B_y	Top Metal Size	1380 1380
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bond;

b) ***Al-Ni-Ag*** – for Soldering.

Backside metal: ***Ti-Ni-Ag***.